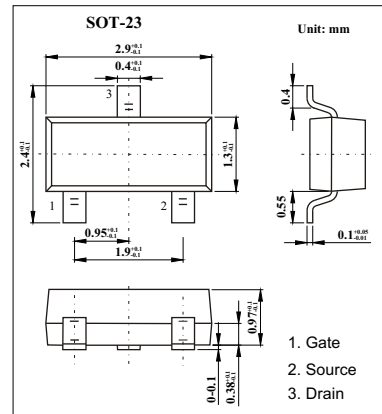
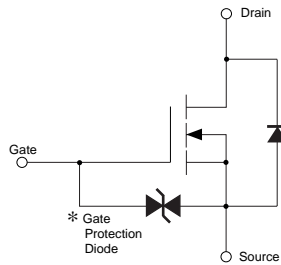


**Features**

- Low on-resistance.
- Fast switching speed.
- Silicon N-channel MOSFET
- Drive circuits can be simple.



**Absolute Maximum Ratings Ta = 25**

Parameter	Symbol	Rating	Unit
Drain-source voltage	V <sub>DSS</sub>	30	V
Gate-source voltage	V <sub>GSS</sub>	± 20	V
Drain current	I <sub>D</sub>	100	mA
	I <sub>DP</sub> * <sup>1</sup>	400	
Total power dissipation	P <sub>D</sub> * <sup>2</sup>	200	mW
Channel to ambient	R <sub>th(ch-a)</sub> * <sup>2</sup>	625	/W
Channel Temperature	T <sub>ch</sub>	150	
Storage temperature	T <sub>stg</sub>	-55 to +150	

\*1. Pw 10μs, duty cycle 1%.

\*2. With each pin mounted on the recommended lands.

Electrical Characteristics Ta = 25

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Gate-source leakage	IGSS	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$			$\pm 1$	$\mu\text{A}$
Drain-source Breakdown voltage	$V_{(BR)DSS}$	$I_D = 10\ \mu\text{A}, V_{GS} = 0\text{V}$	30			V
Zero gate voltage drain current	IDSS	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{V}$			1	$\mu\text{A}$
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = 3\text{ V}, I_D = 100\ \mu\text{A}$	0.8		1.5	V
Static drain-source on-state resistance	$R_{DS(on)}$	$I_D = 10\text{ mA}, V_{GS} = 4\text{V}$ $I_D = 1\text{mA}, V_{GS} = 2.5\text{V}$		5 7	8 13	
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 3\text{ V}, I_D = 10\text{ mA}$	20			mS
Input capacitance	Ciss	$V_{DS} = 5\text{ V},$		13		pF
Output capacitance	Coss	$V_{DS} = 0\text{ V},$		9		pF
Reverse transfer capacitance	Crss	$f = 1\text{MHz}$		4		pF
Turn-on delay time	$t_{d(on)}$	$I_D = 10\text{ mA}, V_{DD} = 5\text{ V},$		15		ns
Rise time	tr	$V_{GS} = 5\text{ V},$		35		ns
Turn-off time	$t_{d(off)}$	$R_L = 500$		80		ns
Fall time	tr	$R_G = 10$		80		ns